

IN THE CLAIMS:

Please cancel claims 2, 5, and 6 without prejudice to or disclaimer of the subject matter recited therein.

Please amend claims 1 and 3 and add new claim 7 as follows:

LISTING OF CURRENT CLAIMS

Claim 1. (Currently Amended) An active matrix organic electroluminescence display device, comprising:

a thin film transistor, comprising:

a gate metal disposed on a substrate;

5 a dielectric insulation layer covering said gate metal and said substrate;

a source/drain metal disposed on said dielectric insulation layer and above said gate metal; and

10 a passivation layer covering said source/drain metal and being a multi-layer structure, wherein said multi-layer structure includes one silicon nitride layer with the thickness of approximately 3000 Å; and

an organic light emitting diode, comprising:

an anode electrode connected to said source/drain metal;

an organic emitting layer formed on said anode electrode; and

15 a cathode electrode formed on said organic emitting layer.

Claim 2. (Canceled)

Claim 3. (Currently Amended) An active matrix organic electroluminescence display device, comprising:

a thin film transistor, comprising:

a gate metal disposed on a substrate;

5 a dielectric insulation layer covering said gate metal and said substrate;

a source/drain metal disposed on said dielectric insulation layer and above said gate metal; and

10 a passivation layer covering said source/drain metal, wherein ~~the~~ a surface of said passivation layer is thermally ~~oxidized~~; oxidized; and

an organic light emitting diode, comprising:

an anode electrode connected to said source/drain metal;

an organic emitting layer formed on said anode electrode; and

a cathode electrode formed on said organic emitting layer.

Claim 4. (Original) The active matrix organic electroluminescence display device of Claim 3, wherein said passivation layer is made of SiNx and the surface thereof is thermally oxidized to form SiON.

Claims 5-6. (Canceled)

Claim 7. (New) The active matrix organic electroluminescence display device of Claim 1, wherein said multi-layer structure includes at least two SiNx layers, each layer of which approximately has a thickness of 3000 Å.